

Sergei I Kozlovskiy

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Multi-ion scattering of charged carriers by ionized impurities in heavily doped semiconductors: From bulk to nanowires. Journal of Applied Physics, 2022, 131, 125708. | 2.5 | 1 |
| 2 | Electron Mobility in Molybdenum Disulfide: From Bulk to Monolayer. Physica Status Solidi (B): Basic Research, 2020, 257, 1900635. | 1.5 | 2 |
| 3 | Ionized impurity scattering in quantum wells and quantum wires. Journal of Applied Physics, 2020, 128, 174301. | 2.5 | 4 |
| 4 | Strain induced mobility enhancement in p-type silicon structures: Bulk and quantum well (quantum) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5 | 2.5 | 3 |
| 5 | A quantum kinetic approach for calculating low-field mobility in black phosphorus crystals and multilayer phosphorene. Journal of Computational Electronics, 2018, 17, 1549-1556. | 2.5 | 2 |
| 6 | Quantum kinetics approach to calculation of the low field mobility in the hole inversion layers of silicon MOSFETs. Journal of Computational Electronics, 2018, 17, 926-933. | 2.5 | 1 |
| 7 | Dilatation deformation potential, drift mobility and piezoresistance in p-type silicon (quantum kinetic) Tj ETQq1 1 0,784314 rgBT /Overlock 4 | 2.5 | 4 |
| 8 | Piezoresistance effect in n-type silicon: from bulk to nanowires. Journal of Computational Electronics, 2014, 13, 515-528. | 2.5 | 4 |
| 9 | Longitudinal piezoresistance and conductance of the p-type silicon nanostructures in ballistic transport regime: from bulk to nanowires. Journal of Computational Electronics, 2012, 11, 203-215. | 2.5 | 0 |
| 10 | Piezoresistive effect in p-type silicon classical nanowires at high uniaxial strains. Journal of Computational Electronics, 2011, 10, 258-267. | 2.5 | 10 |
| 11 | Investigation of conductivity and piezoresistance of n-type silicon on basis of quantum kinetic equation and model distribution function. Sensors and Actuators A: Physical, 2008, 147, 17-33. | 4.1 | 14 |
| 12 | First-order piezoresistance coefficients in heavily doped p-type silicon crystals. Sensors and Actuators A: Physical, 2007, 133, 72-81. | 4.1 | 15 |
| 13 | A silicon stress-sensitive unijunction transistor. Technical Physics, 2002, 47, 438-443. | 0.7 | 3 |